



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

60 A

Features

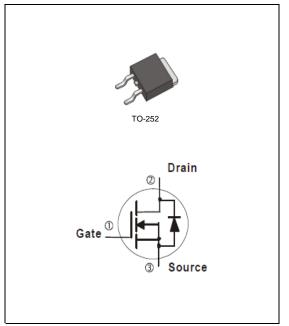
- RDS(ON), VGS@10V, ID@30A<10m Ω
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

• Case: TO-252 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	l _D	60	A	
	T _C =100°C		38		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	240		
Power Dissipation	T _C =25°C	Po	72		
	T _C =100°C		29	W	
Continuous Drain Current	T _A =25°C	I _D	10	Α	
	T _A =70°C		8	Α	
Power Dissipation	T _A =25°C		2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	180	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	1.7	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	60	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	2.0	2.8	3.5	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =30A	-	8.4	10	mΩ		
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =48V, V_{GS} =0V	-	-	1.0	uA		
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 7)								
Total Gate Charge	Q_g	V _{DS} =48V, I _D =25A, V _{GS} =10V ^(Note 1,2)	-	52	-	nC		
Gate-Source Charge	Q_gs		-	11	-			
Gate-Drain Charge	Q_{gd}		-	15	-			
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	2904	-	pF		
Output Capacitance	Coss		-	241	-			
Reverse Transfer Capacitance	Crss	I=1.0IVIHZ	-	112	-			
Turn-On Delay Time	td _(on)	\/ 00\/ L 00A	-	18	-			
Turn-On Rise Time	t _r	V_{DD} =30V, I_{D} =30A, V_{GS} =10V, R_{G} =3.3 Ω (Note 1,2)	-	48	-			
Turn-Off Delay Time	td _(off)		-	54	-			
Turn-Off Fall Time	t _f	K _G =3.312	-	18	-			
Drain-Source Diode								
Maximum Continuous Drain-Source					60	^		
Diode Forward Current	I _S		-	-	60	Α		
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.7	1.2	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =60A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

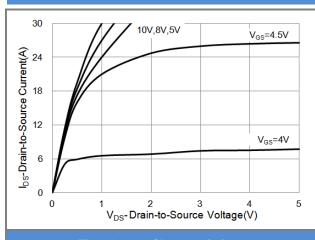


Fig.1 Output Characteristics

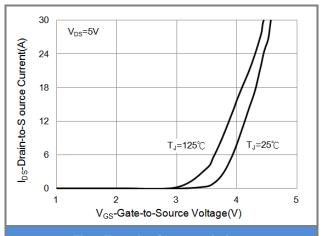


Fig.2 Transfer Characteristics

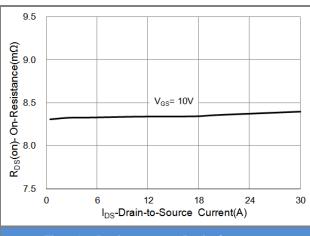


Fig.3 On-Resistance vs. Drain Current

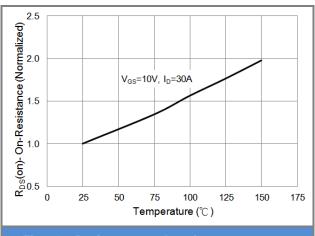


Fig.4 On-Resistance vs. Junction temperature

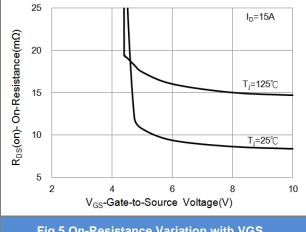


Fig.5 On-Resistance Variation with VGS.

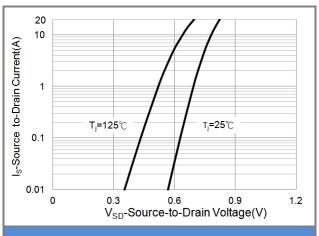


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

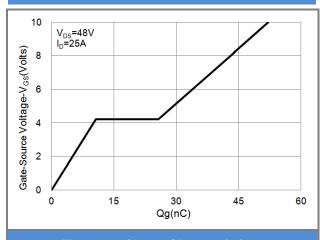


Fig.7 Gate-Charge Characteristics

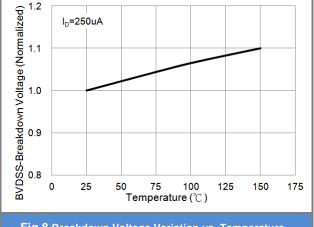


Fig.8 Breakdown Voltage Variation vs. Temperature

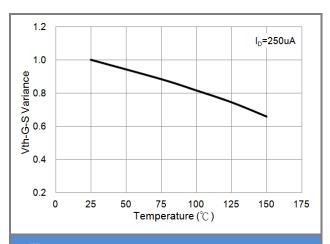


Fig.9 Threshold Voltage Variation with Temperature

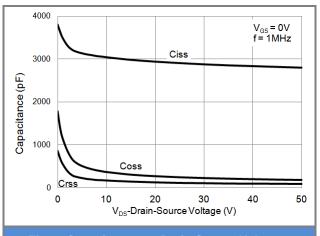


Fig.10 Capacitance vs. Drain-Source Voltage

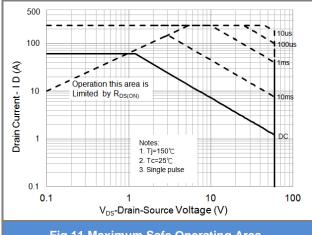


Fig.11 Maximum Safe Operating Area





TYPICAL CHARACTERISTIC CURVES

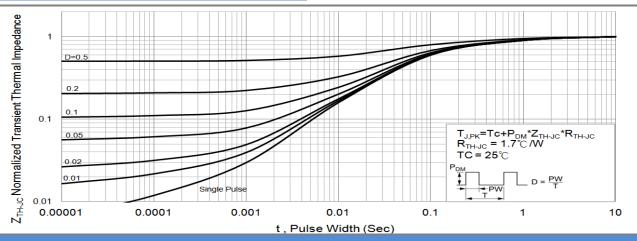
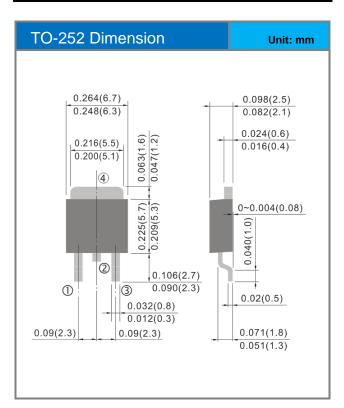


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





Packaging Information



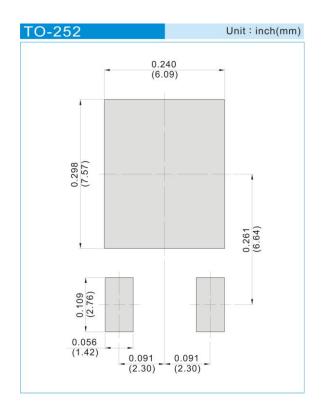




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version	
PJD60N06_L2_00001	TO-252	3,000pcs / 13" reel	D60N06	Halogen free	

MOUNTING PAD LAYOUT







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